JST CREST/DVLSI

Architecture and Circuits for Dependable 3D-VLSI

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Why 3D ?

Is the Future Repartitioning ?

What Does 3D Buy Us?



Byran Black, CTO of AMD at Global Interposer Conf Nov 2011

Black claims that AMD has been involved in 3D for more than 5 years but adds that they are "... intentionally not talking about what we're doing."

"Southbridge (22 nm) is probably the last chip that will be impacted by scaling"

In the future focus will be on specific application functionalities to: --

- reduce mask layers
- reduce run time, power requirements, area and cost
- increase yield while improving performance

These separately fabricated functionalities will be combined vertically and/or horizontally on an interposer to form the final circuit function.



Ivo Bolsens (Xilinx CTO), 3D-Architectures for Semiconductor Integration and Packaging, San Francisco, December 12-14, 2011

The First Wave of 3D ICs

ElectronicsWeekly.com IBM Demonstrates 3D Chip Technology in Micron Memory Cube

IBM has announced that Micron will begin production of Richard Wilson IBM has announced that Micron will begin production of a memory device built using its commercial CMOS manufacturing technology to employ through-ailcon vias ITSVI-(TSVs)-

DRAM Layers COMPUTERWORLD Apple's A6 processor: 28-nm, 3D IC and made by TSMC

White we wait for Lion, interesting to note the next Apple Write we wait for Lion, marriesting to note the next Apple (AAPL) 46 processor will be made by Talwan Semiconductor Manufacturing Co. (TSMC) and will be a set or semiconductor for Antifacturing contents of the set 3D IC 28-narometer low-power powerhouse, sweetly au re-re-nanomene rom-power powernance, seven bucked inside your iPhones and future model iPade.

12 level metal

TSV capture level.



EE Times Perfecting the 3-D chip R. . Inhoson

10/110. 11 10.2 You've heard the hype.... frundation of semiconductor fabrication will be transformed over the next few years as multistory structures rise up from dice that today are planar. After almost a decade of major semiconductor engineering efforts worldwide almed at making the structures manufacturable, three-dimensional ICs are poised for commercialization starting next year-several years behind schedule.

MercuryNews.com New efforts to extend Moore's Law

By Steve Johnson Continually needing to add computing power to its microprocessors, Santa Clara behemoth Intel (INTC) this year announced it was venturing beyond its traditional method of cramming more and more transistors into a flat pieces of silicon in favor of a different approach - building chips in three dimensions.



Micron reveals "Hyper Memory Cube" 3DIC Technology

A few weeks ago Mark Durcan, COO of Mcron, at the IEEE A fore weaks ago Mark Durcen, CC/O of Micron, at the little ISS meeting in hair Moon Bay commented that Micron is "sampling products based on TSVs" and that Micron is neurosciences are rest formed and other more service for the service "sampling products based on 15Vs" and mit: trass production for TSV-based 3-D chips are stated for the next



Octuber 25, 2011, 10:50 AM ET Xilinx Says Four Chips Act Like One Giant

Chip makers have been living by Moore's Law for Long reasons a new open symplery involute a Law rok decades. But that pace of progress is not fast anough for some people, and Xilvix thinks it can help





2.5D and 3D FPGA (Xilinx)





3D System Integration (IBM)







3D-eDRAM for L3 Cache (IBM)

Hybrid Memory Cube (HMC) (Micron+Samsung+IBM)

THE WALL STREET JOURNAL

By Don Clark

Intel co-founder Gordon Moore, in the observation that inter op tourion value of the transmission water and the strength of the stren relentiess shrinking of the size and on

Dependability Related Concerns in 3D VLSI

- Heat accumulation and heat removal
- Influences of mechanical stress
- Metal impurity contamination
- Reliabilities of TSV's and metal microbumps
- Design methodology and design tools
- Testing and test design



Application of 3D VLSI to Image Processing VLSI for Automobile

Target : ISO 26262 ASIL=C



<Relation between Requirements by Application and Various Technologies>

After T. Kamada (Denso)

Architecture of 3D DVLSI System



After Prof. H. Kobayashi (Tohoku Univ.)

The Measure for A Reliability Target

• Fault converge 97%



- A timing error occurs in a hot spot.

-80FIT



Quantitive analysis is needed. ↓ It comes back to the reliability of a majority circuit, and throughput/parallelism.

After T. Kamada (Denso)

Test Architecture for 3D VLSI with Redundant Tiers



Block Diagram of 3D DVLSI (e.g. 4tiers)



Self-Test Control by System-Level SVP in 3D Dependable VLSI System

- SVP (Supervisor Processor) controls TAP and Chain in the stacked 3D dependable LSI
 - Drives TCK, TMS, TRST, TDI
 - Read TDO to get test data registers in the stacked dice
- ✓ Assuming TAP signals are connected by quadruple TSV that has much higher reliability than single TSV



3D DfT Architecture

Functional Design

- ≥4 Stacked Dies, Core-Based
- Inter-Connect: TSVs
- Extra-Connect: Pins

Existing Design-for-Test

- Core: Internal Scan, TDC, LBIST, MBIST; IEEE 1149.1 wrappers, TAPC
- Stack Product: IEEE Std 1149.1
- **3D-DfT Architecture -** Test Wrapper per Die
 - Based on IEEE 1149.1
 - Two Entry/Exit Points per Die:
 - Pre-Bond : Extra Probe Pads
 - Post-Bond: Extra TSVs

New 3D VLSI DfT Architecture for Online Self-Test of Dies Based on IEEE 1149.1.



Tier BIST Dynamically Controlled by System-Level SVP

from/to Sys-SVP



Redundancy for Through Si Vias (TSVs)

		No Repair	Multiplexed TSV		With TSV Repair	
			m: multiplicity		n signals : r redundant TSVs	
			2	4	4:2	16:4
Area		+0%	+100%	+300%	+50%	+25%
Capacity		+0%	+100%	+300%	+0%	+0%
Switches/Sig		0	0	0	3	5
TSV Group Yield (n TSVs)		(R _{TSV}) ⁿ	$(1 - (1 - R_{TSV})^m)^n$		$\sum_{i=n}^{n+r} \binom{n+r}{i} R_{TSV}^{i}$	$(1 - R_{TSV})^{n+r-i}$
Assembly Yield *	2,000	$1.9\times10^{-7}\%$	81.87%	99.99%	99.03%	99.98%
	5,000	1.5×10^{-20} %	60.65%	99.99%	97.59%	99.96%
	10,000	$2.2\times10^{-42}\%$	36.79%	99.99%	95.23%	99.91%
	20,000	5.1×10^{-86} %	13.53%	99.98%	90.69%	99.83%
Samsung (ISSCC 2009) This Work						

*assumed $R_{TSV} = 0.99$

Approach for HW-SVP

- Establishing a self-repair scheme for HW-SVP
 - Soft-error recovery using dynamic reconfiguration
 - Designing recovery controller and Scrubbing controller
 - Designing fault-tolerant system using TMR scheme

Developing Evaluation system to evaluate soft-error tolerability

Hard-error avoidance using partial reconfiguration

- Relocating partial reconfiguration bitstream (PRB)
- Designing TMR scheme with Spare

TMR : Triple Modular Redundancy

Self-repair scheme and Evaluation system

System Configuration of HW-SVP



Implemented on : Xilinx Virtex-6 XC6VLX240T

- Triplicating processor core and peripheral modules
- Implementing RM, RC and Spare
 - RM and RC control recovery sequence
 - Spare is used for hard-error avoidance

RC : Recovery Controller RM : Recovery Module ICAP : Internal Configuration Access Port

Soft-Error Recovery in HW-SVP

Readback and Overwrite reconfiguration (Scrubbing)



Hard-Error Recovery in HW-SVP

Relocate PRB and separate a broken module



Implementing a copy of Module on Spare to reconstruct TMR configuration

* This is realized by uniforming inner configuration of PR region (reported on Dec. 2011)